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SN74GTLP817 GTLP-TO-LVTTL 1-TO-6 FANOUT DRIVER

SCES285E-OCTOBER 1999-REVISED APRIL 2005

FEATURES

- OEC[™] Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference
- Bidirectional Interface Between GTLP Signal Levels and LVTTL Logic Levels
- GTLP-to-LVTTL 1-to-6 Fanout Driver
- LVTTL-to-GTLP 1-to-2 Fanout Driver
- LVTTL Interfaces Are 5-V Tolerant
- Medium-Drive GTLP Outputs (50 mA)
- Reduced-Drive LVTTL Outputs (-12 mA/12 mA)
- Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in Distributed Loads
- I_{off} and Power-Up 3-State Support Hot Insertion
- Distributed V_{CC} and GND Pins Minimize High-Speed Switching Noise
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DGV, DW, OR PW PACKAGE (TOP VIEW) AI Π 1 24 Π GNDT 23 OEAB AO1 2 GNDT 3 22 BO1 21 GNDG AO2 4 V_{CC} 5 20 V_{RFF} AO3 🛮 6 19 GNDG GNDT 7 18 🛮 ERC 17 BO2 AO4 8 16 GNDG V_{CC} 49 15 🛮 BI AO5 10 14 OEBA GNDT 11 AO6 **GNDT**

DESCRIPTION/ORDERING INFORMATION

The SN74GTLP817 is a medium-drive fanout driver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard TTL or LVTTL) backplane operation is a direct result of GTLP reduced output swing (<1 V), reduced input threshold levels, improved differential input, and OECTM circuitry. The improved GTLP OEC circuitry minimizes bus settling time and has been designed and tested using several backplane models. The medium drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 19 Ω . BO1 and BO2 can be tied together to drive an equivalent load impedance down to 11 Ω .

GTLP is the Texas Instruments (TITM) derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLP817 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTLP ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs. V_{REF} is the B-port differential input reference voltage.

GNDT is the TTL output ground, while GNDG is the GTLP output ground, and both may be separated from each other for a quieter device.

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DESCRIPTION/ORDERING INFORMATION (CONTINUED)

This device is fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

This device features adjustable edge-rate control (ERC). Changing the ERC input voltage between GND and V_{CC} adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load. ERC automatically is selected to the same speed as alternate source 1-to-6 fanout drivers that use pin 18 for 3.3-V or 5-V V_{CC} .

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable (\overline{OE}) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

ORDERING INFORMATION

T _A	PACK	AGE ⁽¹⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC – DW	Tube	SN74GTLP817DW	GTLP817
-40°C to 85°C	SOIC - DW	Tape and reel SN74GTLP817DWR		GILPOIT
	TSSOP - PW	Tape and reel	SN74GTLP817PWR	GT817
	TVSOP – DGV Tape and reel		SN74GTLP817DGVR	GT817

⁽¹⁾ Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTIONAL DESCRIPTION

The SN74GTLP817 is a fanout driver providing LVTTL-to-GTLP translation and GTLP-to-LVTTL translation in the same package.

The LVTTL-to-GTLP direction is a 1-to-2 fanout driver with a single output enable (OEAB).

The GTLP-to-LVTTL direction is a 1-to-6 fanout driver with a single output enable (OEBA).

Data polarity is inverting for both directions.



FUNCTION TABLES

OUTPUT CONTROL (A TO B)

INF	PUTS	OUTPUT	MODE			
Al	OEAB	BOn	MODE			
Х	Н	Z	Isolation			
Н	L	L	Invested transparent			
L	L	Н	Inverted transparent			

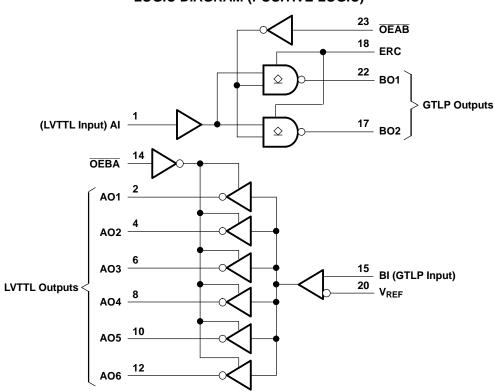
OUTPUT CONTROL (B TO A)

INF	PUTS	OUTPUT	MODE			
ВІ	OEBA	AOn	MODE			
Х	Н	Z	Isolation			
Н	L	L	Invested transparent			
L	L	Н	Inverted transparent			

B-PORT EDGE-RATE CONTROL (ERC)

INI	PUT ERC	OUTPUT
LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
Н	V _{CC}	Slow
L	GND	Fast

LOGIC DIAGRAM (POSITIVE LOGIC)



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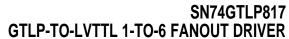
Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range	-0.5	4.6	V	
V _{GNDG} - V _{GNDT}	Ground dc voltage difference			0.3	V
V	Input voltage range (2)	Al port and control inputs	-0.5	7	V
V _I	Input voltage range ⁽²⁾	BI port and V _{REF}	-0.5	4.6	V
M	Voltage range applied to any output in the	AO port	-0.5	7	V
Vo	high-impedance or power-off state (2)	BO port	-0.5	4.6	V
	Comment into any output in the law state	AO port		24	A
Io	Current into any output in the low state	BO port		100	mA
Io	Current into any A output in the high state (3)			24	mA
	Continuous current through each V _{CC} or GNI)		±100	mA
I _{IK}	Input clamp current	V ₁ < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
		DGV package		86	
θ_{JA}	Package thermal impedance ⁽⁴⁾	DW package		46	°C/W
		PW package			
T _{stg}	Storage temperature range		-65	150	°C

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

 ⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 (3) This current flows only when the output is in the high state and V_O > V_{CC}.
 (4) The package thermal impedance is calculated in accordance with JESD 51-7.





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Recommended Operating Conditions (1)(2)(3)(4)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		3.15	3.3	3.45	V
V	Tormination valtage	GTL	1.14	1.2	1.26	V
V_{TT}	Termination voltage	GTLP	1.35	1.5	1.65	V
V	Defenses valters	GTL	0.74	0.8	0.87	
V_{REF}	Reference voltage	GTLP	0.87	1	1.1	V
	land or line	BI			V_{TT}	
V_{I}	Input voltage	AI, OE		V _{CC}	5.5	V
		BI	V _{REF} + 0.05			
V_{IH}	High-level input voltage	ERC	V _{CC} - 0.6	V _{CC}	5.5	V
		AI, OE	2			
		BI			V _{REF} - 0.05	
V_{IL}	Low-level input voltage	ERC		GND	0.6	V
		AI, OE			0.8	
I _{IK}	Input clamp current				-18	mA
I _{OH}	High-level output current	AO port			-12	mA
	Landan dan dan dan dan dan dan dan dan da	AO port			12	Δ
l _{OL}	Low-level output current	ow-level output current BO port			50	mA
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		20			μs/V
T _A	Operating free-air temperature		-40		85	°C

 ⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.
 (2) Normal connection sequence is GND first and V_{CC} = 3.3 V, I/O, control inputs, V_{TT}, V_{REF} (any order) last.
 (3) V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances if the dc recommended I_{OL} ratings are not exceeded.
 (4) V_{REF} can be adjusted to optimize noise margins, but normally is two-thirds V_{TT}.

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Electrical Characteristics

over recommended operating free-air temperature range for GTLP (unless otherwise noted)

F	PARAMETER	TEST CONDITION	NS	MIN TYP(1)	MAX	UNIT
V _{IK}		V _{CC} = 3.15 V,	I _I = -18 mA		-1.2	V
		V _{CC} = 3.15 V to 3.45 V,	$I_{OH} = -100 \mu A$	V _{CC} - 0.2		
.,	AO nort		$I_{OH} = -100 \mu A$	V _{CC} - 0.2		V
V _{OH}	AO port	V _{CC} = 3.15 V	$I_{OH} = -6 \text{ mA}$	2.4		V
			$I_{OH} = -12 \text{ mA}$	2.2		
		V _{CC} = 3.15 V to 3.45 V,	I _{OL} = 100 μA		0.2	
	AO nort		I _{OL} = 100 μA		0.2	
	AO port	V _{CC} = 3.15 V	I _{OL} = 6 mA		0.4	
V_{OL}					0.5	V
			I _{OL} = 100 μA		0.2	Ť
	BO port	V _{CC} = 3.15 V	$I_{OL} = 40 \text{ mA}$		0.5	
			$I_{OL} = 50 \text{ mA}$		0.55	
I	BI, AI, OE, ERC	V _{CC} = 3.45 V,	$V_1 = 0 \text{ or } 5.5 \text{ V}$		±5	μΑ
	AO port	V 2.45.V	$V_O = V_{CC}$		10	^
I _{OZH}	BO port	$V_{CC} = 3.45 \text{ V}$	V _O = 1.5 V		5	μΑ
	AO port	V 0.45 V	V _O = GND		-10	Δ.
I _{OZL}	BO port	$V_{CC} = 3.45 \text{ V}$	V _O = 5.5 V		-5	μΑ
		V _{CC} = 3.45 V, I _O = 0,	Outputs high		10	
I _{CC}	AO or BO port	V_I (Al or control input) = V_{CC} or GND,	Outputs low	10		mA
		V_I (BI input) = V_{TT} or GND	Outputs disabled		10	
$\Delta I_{CC}^{(2)}$	AI, ŌĒ	V _{CC} = 3.45 V, One A-port or control input Other A-port or control inputs at V _{CC} or G			1	mA
_	AI, OE , ERC	$V_I = V_{CC}$ or 0		4	4.4	-
C _i	ВІ	V _I = V _{TT} or 0		3.5	3.9	pF
_	AO port	V _O = V _{CC} or 0		4	4.5	
C _o	BO port	$V_O = V_{TT}$ or 0		5	5.4	pF

Hot-Insertion Specifications for A Port

over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS				
I _{off}	$V_{CC} = 0$,	V_I or $V_O = 0$ to 5.5 V			10	μΑ
l _{OZPU}	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 \text{ V to 3 V},$	$\overline{OE} = 0$		±30	μΑ
I _{OZPD}	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0		±30	μΑ

Hot-Insertion Specifications for B Port

over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
l _{off}	$V_{CC} = 0$,	V_1 or $V_0 = 0$ to 1.5 V			10	μΑ
I _{OZPU}	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 \text{ V to } 1.5 \text{ V},$	$\overline{OE} = 0$		±30	μΑ
I _{OZPD}	$V_{CC} = 1.5 \text{ V to } 0,$	$V_O = 0.5 \text{ V to } 1.5 \text{ V},$	OE = 0		±30	μΑ

⁽¹⁾ All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$. (2) This is the increase in supply current for each input that is at the specified LVTTL voltage level, rather than V_{CC} or GND.



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Switching Characteristics

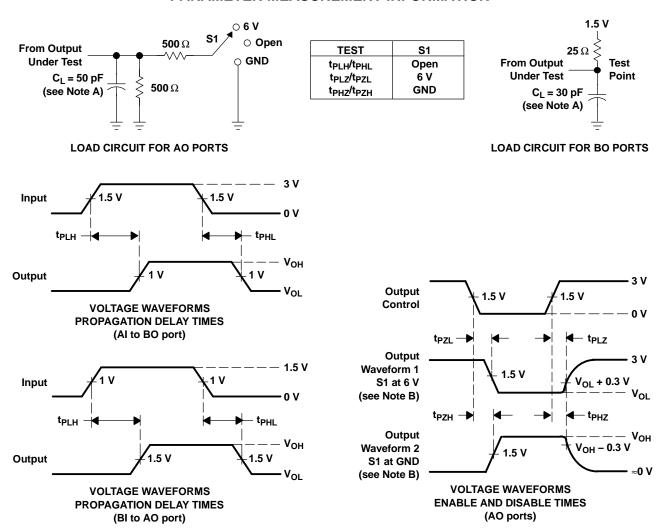
over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE(1)	MIN TYP(2	MAX	UNIT	
t _{PLH}	Al	ВО	Slow	3	6	ne	
t _{PHL}	Al	ВО	Slow	1.8	4.7	ns	
t _{PLH}	Al	ВО	Fast	2	5	ns	
t _{PHL}	Al	ВО	Fasi	1.5	4.2	115	
t _{en}	OEAB	во	Slow	3	6.1	no	
t _{dis}	UEAB	ВО	Siow	2	4.7	ns	
t _{en}	OEAB	ВО	Fast	2.1	6	6 ns	
t _{dis}	UEAB	ВО	Fasi	1.5	4.7	115	
4	Diag time P outp	uto (200/ to 909/)	Slow	2.5		no	
t _r	Rise time, b outp	uts (20% to 80%)	Fast	1.4		ns	
4	Fall time P outpu	Fall time, B outputs (80% to 20%)		1.7		no	
t _f	raii time, b outpo	uis (60% to 20%)	Fast	1		ns	
t _{PLH}	BI	AO		2.3	6	no	
t _{PHL}	ы	AO		1.9	4.7	ns	
t _{en}	OEBA	AO		1.1	6.3	20	
t _{dis}	UEDA	AO		1.2	5	ns	

⁽¹⁾ Slow (ERC = V_{CC}) and Fast (ERC = GND) (2) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \approx 10 MHz, $Z_O = 50~\Omega$, $t_r \approx 2$ ns, $t_f \approx 2$ ns.
 - D. The outputs are measured one at a time, with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



Distributed-Load Backplane Switching Characteristics

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

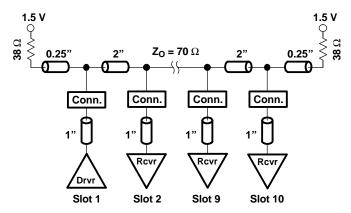


Figure 2. Medium-Drive Test Backplane

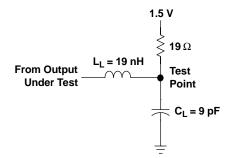


Figure 3. Medium-Drive RLC Network

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Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 3)

11 1021	• • •				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE ⁽¹⁾	TYP ⁽²⁾	UNIT
t _{PLH}	Al	ВО	Slow	4.4	no
t _{PHL}	Al	ВО	Slow	4.4	ns
t _{PLH}	Al	ВО	Fast	3.2	no
t _{PHL}	Al	ВО	Габі	3.2	ns
t _{en}	OEAB	ВО	Slow	4	
t _{dis}	UEAB	ВО	Slow	4.4	ns
t _{en}	OEAB	ВО	Fast	2.9	no
t _{dis}	OEAB	ВО	Габі	3.1	ns
	Dies time Doute	D'action Devices (000) (c. 000)		1.8	
t _r	Rise time, B outp	Rise time, B outputs (20% to 80%)			ns
	Fall time D outs	uto (000/ to 200/)	Slow	2	
t _f	Fall time, B outp	uts (80% to 20%)	Fast	1.6	ns

⁽¹⁾ Slow (ERC = V_{CC}) and Fast (ERC = GND) (2) All typical values are at V_{CC} = 3.3 V, T_A = 25°C. All values are derived from TI-SPICE models.



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74GTLP817PW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GT817	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2022

TUBE

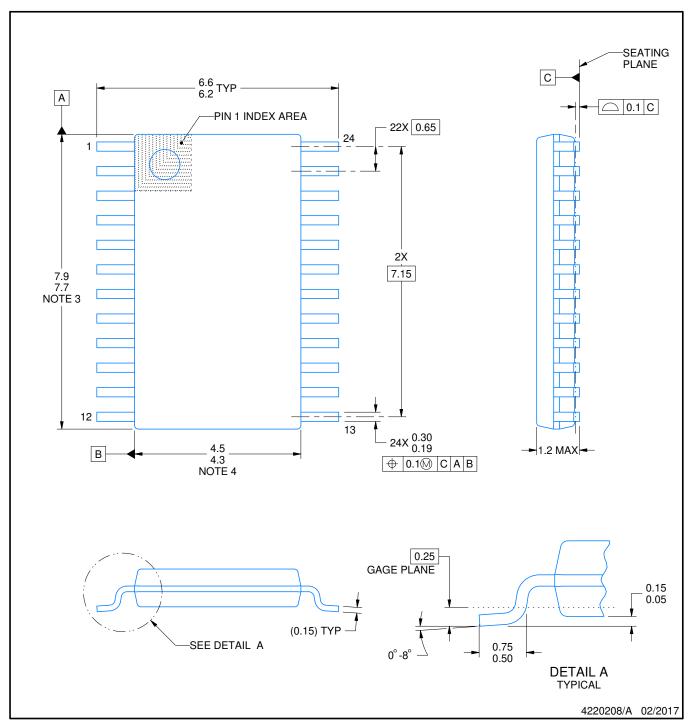


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74GTLP817PW	PW	TSSOP	24	60	530	10.2	3600	3.5



SMALL OUTLINE PACKAGE



NOTES:

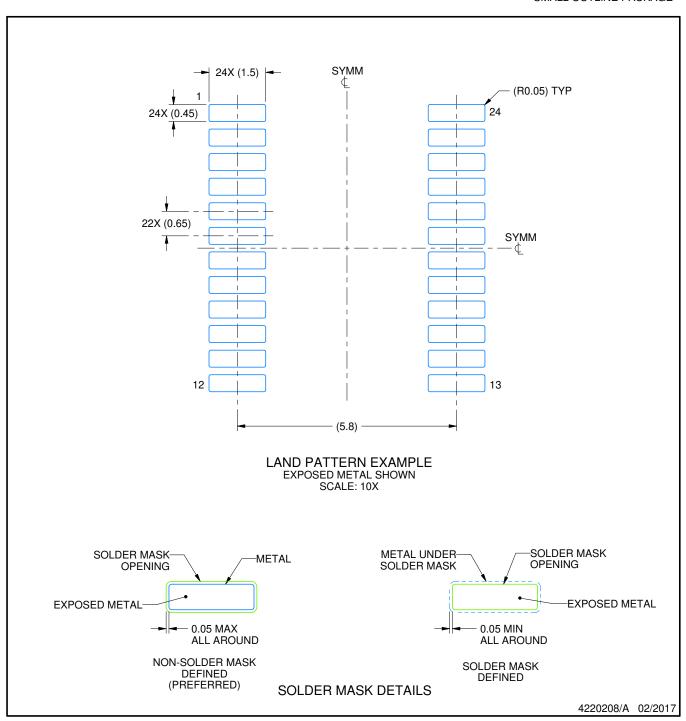
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



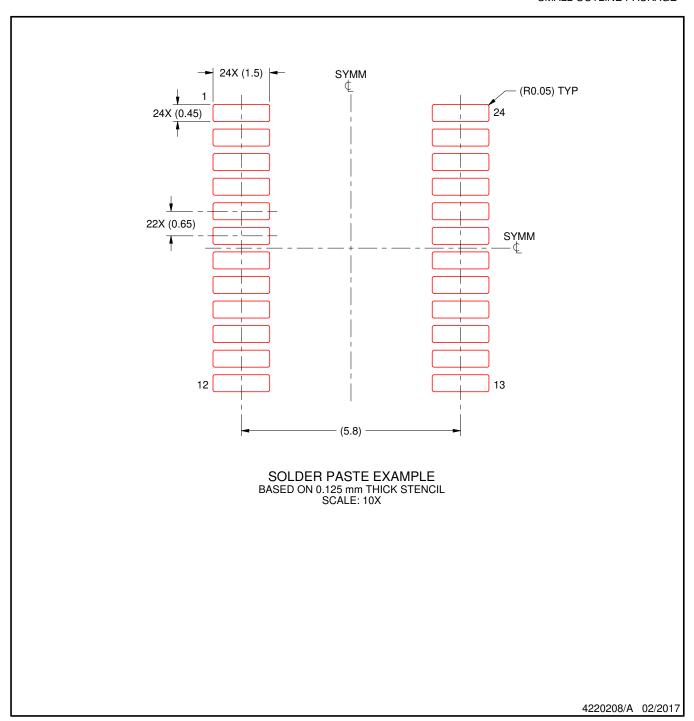
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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